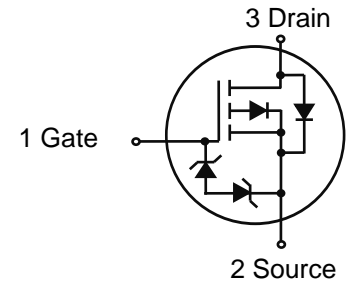
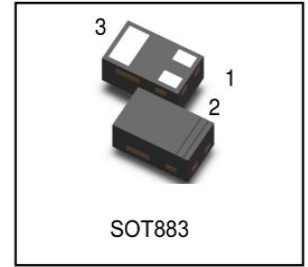


LMP22D5N3T5G

20V P-Channel Enhancement MOSFET



1. FEATURES

- VDS = -20V
- Gate-Source ESD Protected.
- High-Side Switching.
- Low On-Resistance.
- Low Threshold.
- Fast Switching Speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories.
- Battery Operated Systems.
- Power Supply Converter Circuits.
- Load/Power Switching Cell Phones, Pagers.

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMP22D5N3T5G	PG	10000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-to-Source Voltage		VDSS	-20		V
Gate-to-Source Voltage		VGS	±8		V
Continuous Drain Current	TA = 25°C	ID	-850	-700	mA
	TA = 70°C		-670	-600	
Pulsed Drain Current (Note2)		IDM	-2000		
Maximum Power Dissipation (Note1)		PD	350		mW
Operating Junction and Storage Temperature Range		TJ/Tstg	-55~+150		°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Junction-to-Ambient - Steady State (Note 1)	ROJA	357	°C/W

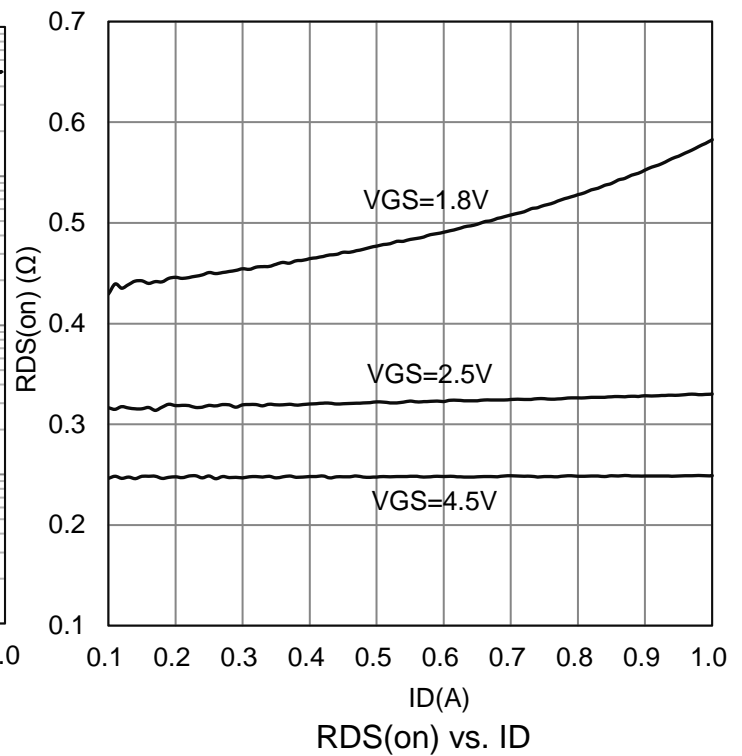
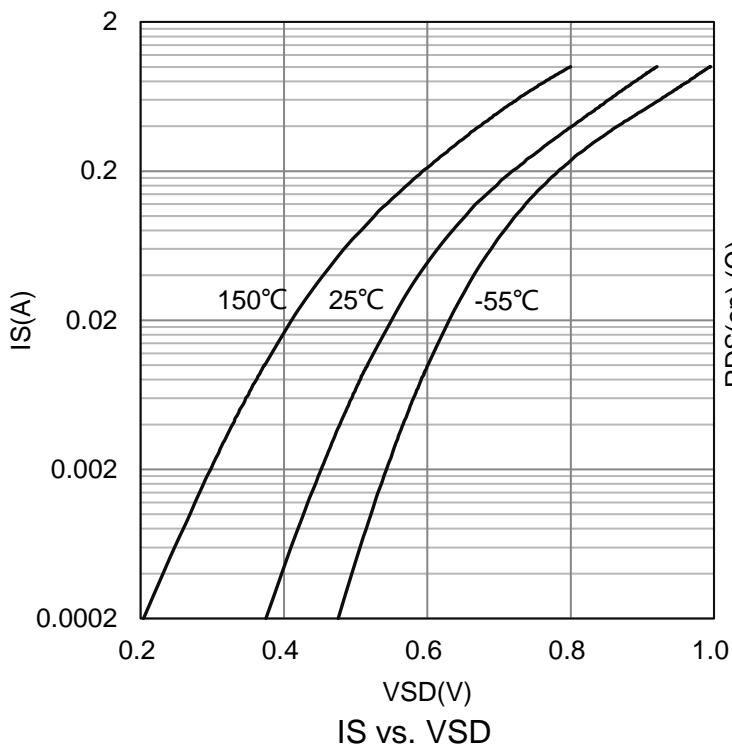
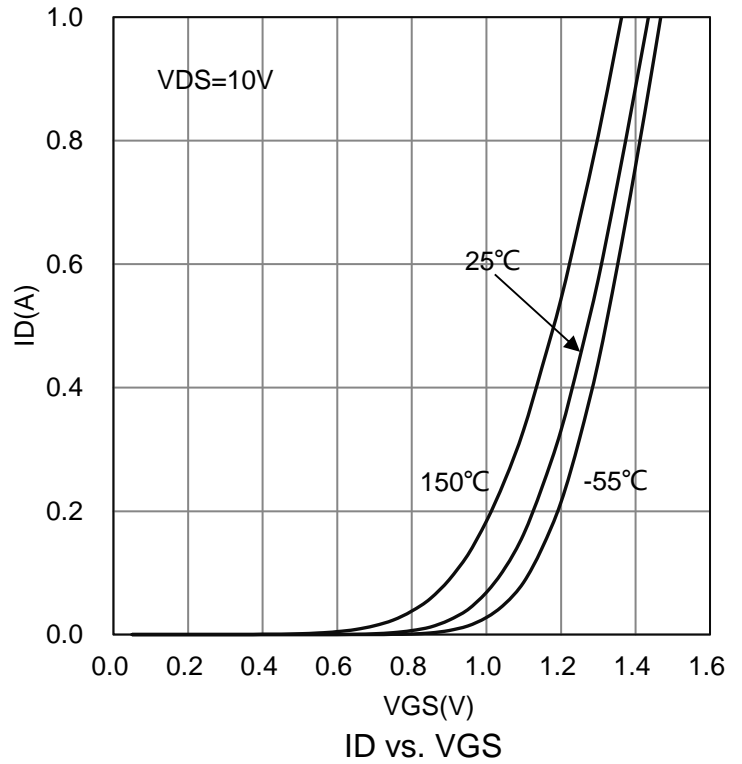
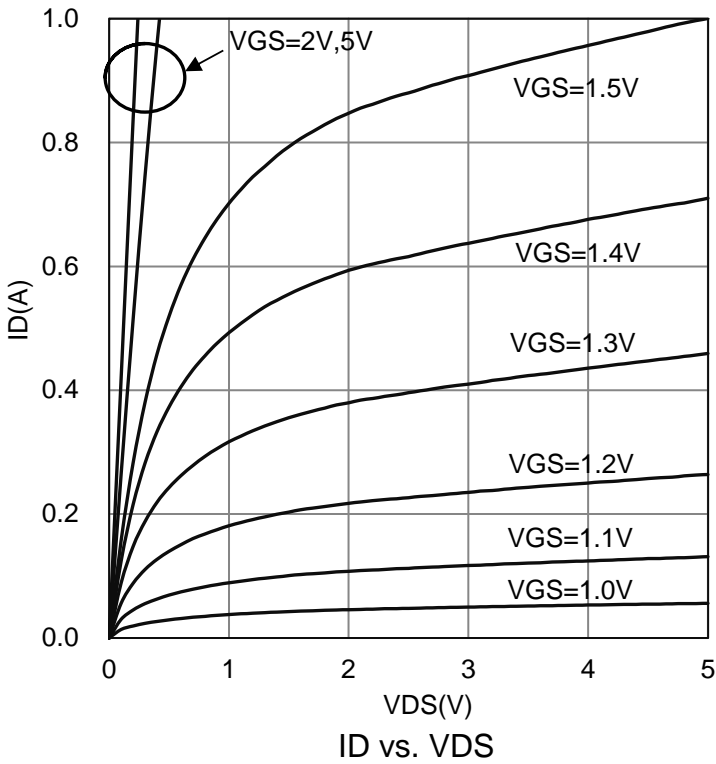
1. FR-4 = 30.0mm×25.0mm×1.6mm
2. Pulse width limited by maximum junction temperature.

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

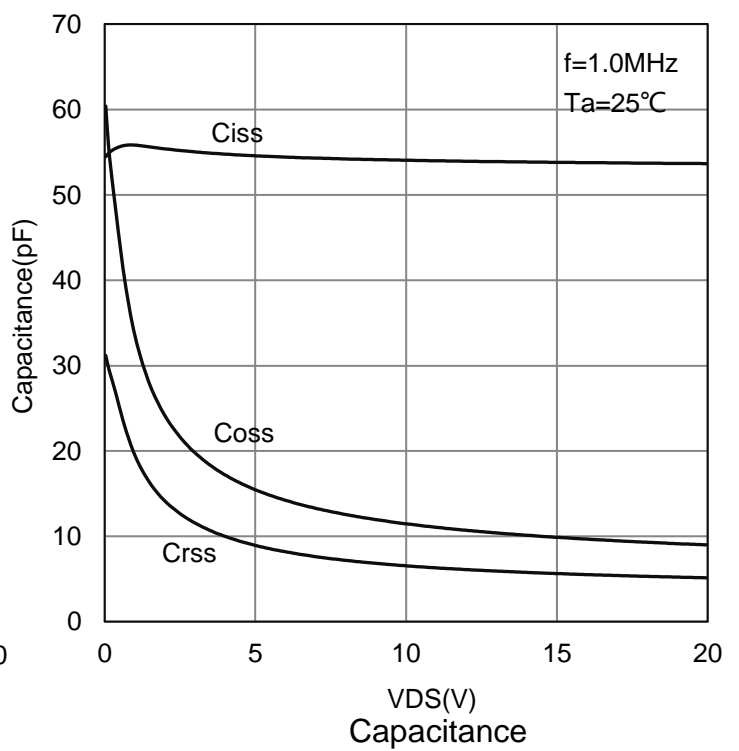
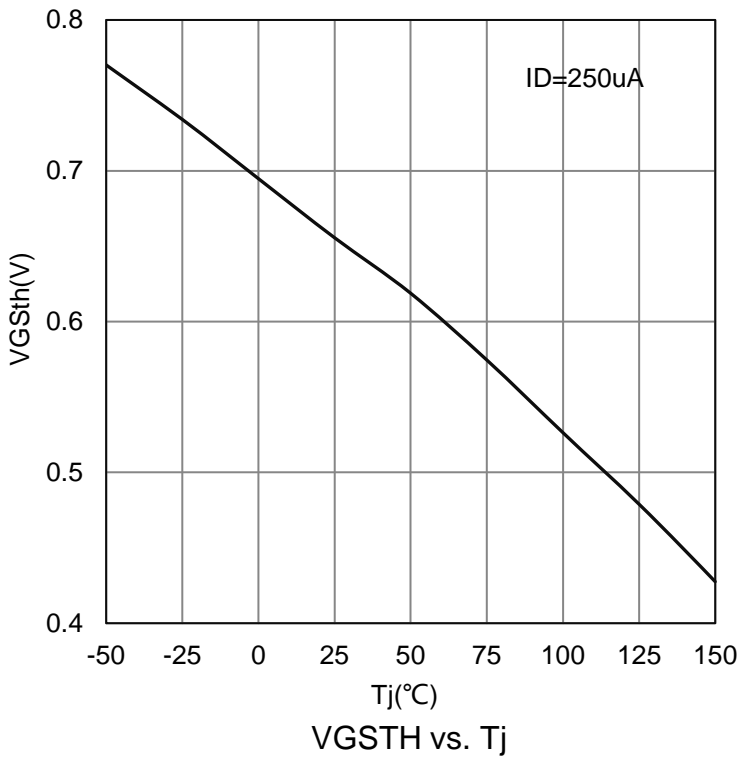
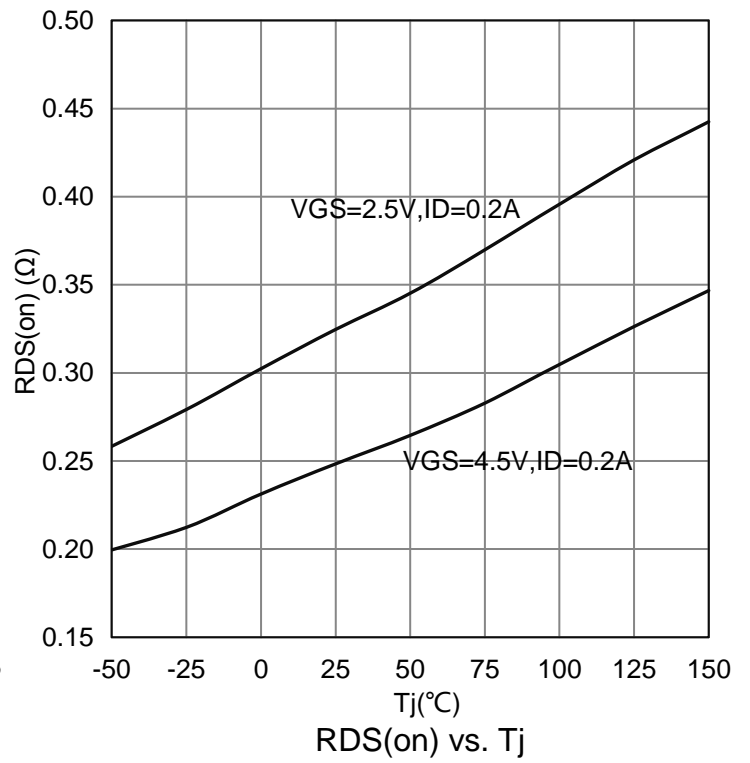
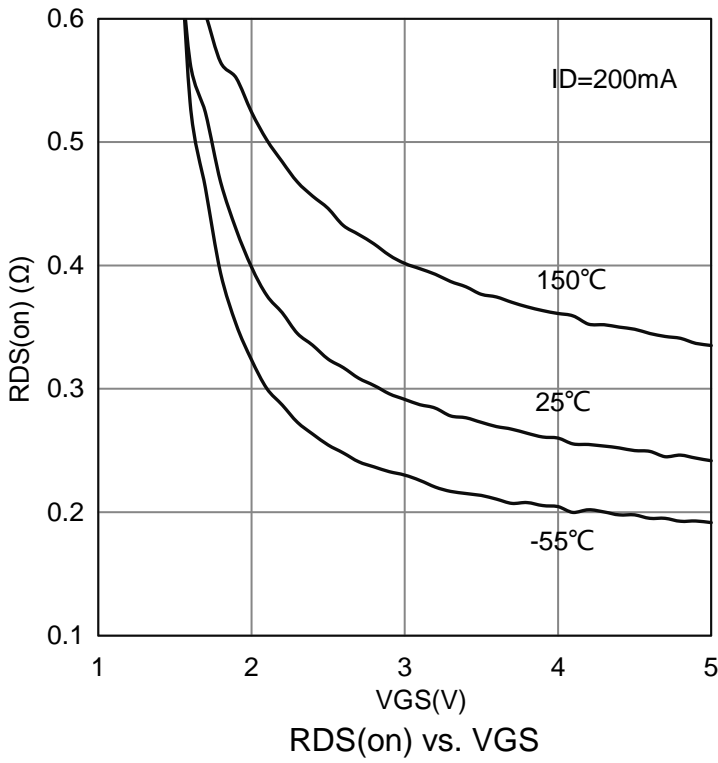
Characteristic	Symbol	Min.	Typ.	Max.	Unit	
Static						
Drain-Source Breakdown Voltage (VGS = 0V, ID =-250uA)	V(BR)DSS	-20	-	-	V	
Gate Threshold Voltage (VDS =VGS , ID =-250μA)	VGS(th)	-0.4	-0.68	-1	V	
Gate Body Leakage Current (VDS =0V, VGS =±8V)	IGSS	-	-	±10	μA	
Zero Gate Voltage Drain Current (VDS =-20V, VGS =0V)	IDSS	-	-	-1	μA	
Drain-Source On-State Resistance (VGS=-4.5V, ID=-0.2A) (VGS=-2.5V, ID=-0.2A) (VGS=-1.8V, ID=-0.2A)	RDS(ON)	-	-	400 500 600	mΩ	
Diode Forward Voltage (IS = -1.0A, VGS = 0V)	VSD	-	-	-1.5	V	
Dynamic						
Total Gate Charge	(VDS =-16V, VGS =-4.5V, ID =-200mA)	Qg	-	1.3	-	nC
Gate-Source Charge		Qgs	-	0.15	-	
Gate-Drain Charge		Qgd	-	0.53	-	
Turn-On Delay Time	(VDD =-10V, RL =50Ω,VGEN =- 5V,RG =10Ω,ID =-200mA)	td(on)	-	26	-	ns
Rise Time		tr	-	66	-	
Turn-Off Delay Time		td(off)	-	82	-	
Fall Time		tf	-	280	-	
Input Capacitance	(VDS = -16 V, VGS = 0 V, f = 1 MHz)	Ciss	-	53	-	pF
Output Capacitance		Coss	-	9.8	-	
Reverse Transfer Capacitance		Crss	-	6.3	-	

3. Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%.

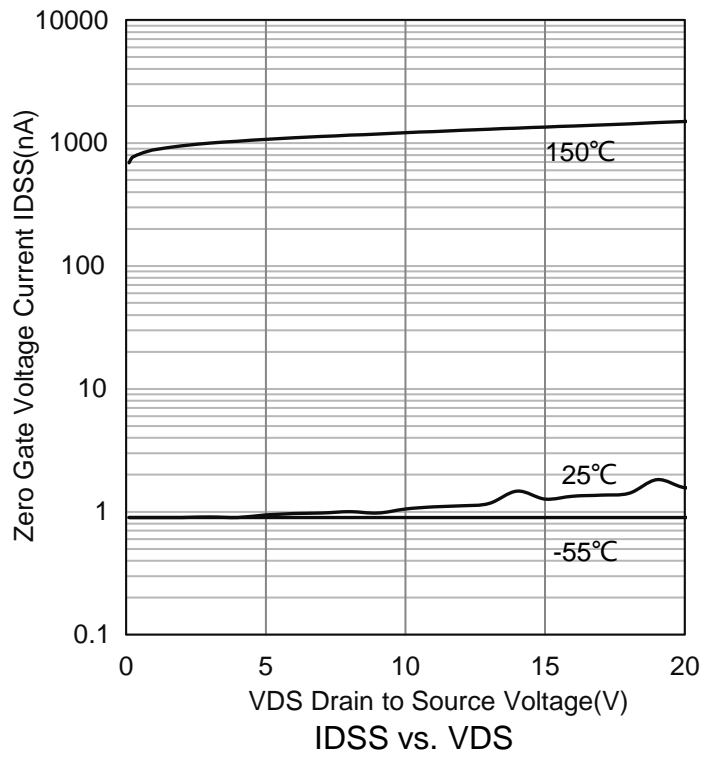
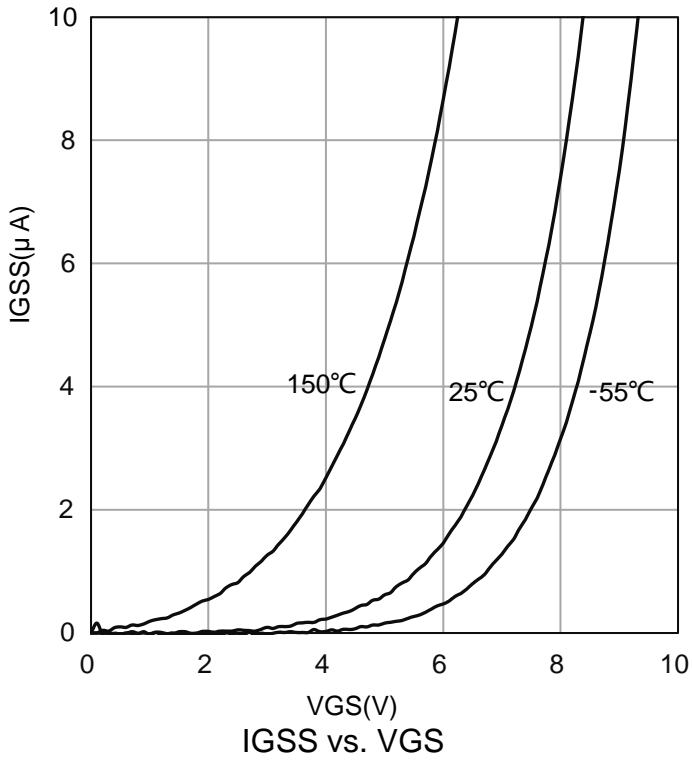
7 ELECTRICAL CHARACTERISTICS CURVES



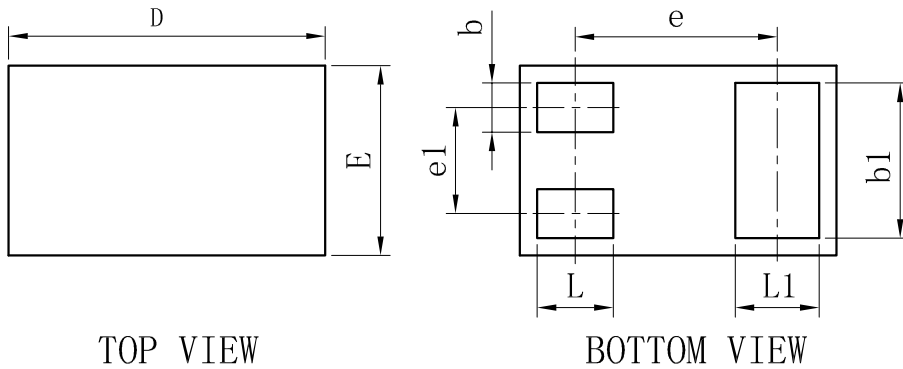
7 .ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

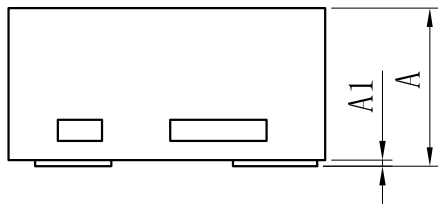


8. OUTLINE AND DIMENSIONS



TOP VIEW

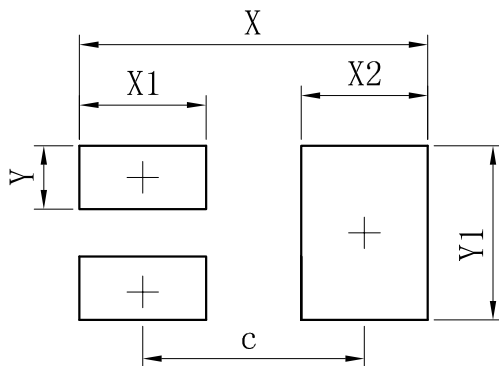
BOTTOM VIEW



SIDE VIEW

SOT883			
Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
e1	-	0.34	-
L	0.19	0.24	0.29
L1	0.22	0.27	0.32
b	0.10	0.15	0.20
b1	0.44	0.49	0.54
A	0.43	0.48	0.53
A1	0	-	0.05
All Dimensions in mm			

9. SOLDERING FOOTPRINT



Dimensions	(mm)
c	0.70
X	1.10
X1	0.40
X2	0.40
Y	0.20
Y1	0.55

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